

# ESD7571, SZESD7571

## Ultra-Low Capacitance ESD Protection

### Micro-Packaged Diodes for ESD Protection

The ESD7571 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, high breakdown voltage, high linearity, low leakage, and fast response time make these parts ideal for ESD protection on designs where board space is at a premium. It has industry leading capacitance linearity over voltage making it ideal for RF applications. This capacitance linearity combined with the extremely small package and low insertion loss makes this part well suited for use in antenna line applications for wireless handsets and terminals.

#### Features

- Industry Leading Capacitance Linearity Over Voltage
- Ultra-Low Capacitance: 0.35 pF Max
- Stand-off Voltage: 5.3 V
- Low Leakage: < 1 nA
- Low Dynamic Resistance: < 1  $\Omega$
- IEC61000-4-2 Level 4 ESD Protection
- 1000 ESD IEC61000-4-2 Strikes  $\pm 8$  kV Contact / Air Discharged
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### Typical Applications

- RF Signal ESD Protection
- RF Switching, PA, and Antenna ESD Protection
- Near Field Communications
- USB 2.0, USB 3.0

#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
IEC 61000-4-2 Contact (ESD) (Note 1) IEC 61000-4-2 Air (ESD) (Note 1)	ESD ESD	$\pm 20$ $\pm 20$	KV kV
IEC 61000-4-5 (ESD) (Note 2)	ESD	2.2	A
Total Power Dissipation (Note 3) @ $T_A = 25^\circ\text{C}$ Thermal Resistance, Junction-to-Ambient	$P_D$ $R_{\theta JA}$	300 400	mW $^\circ\text{C/W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Lead Solder Temperature – Maximum (10 Second Duration)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. At least 10 discharges at  $T_A = 25^\circ\text{C}$ , per IEC61000-4-2 waveform.
2. Non-repetitive current pulse at  $T_A = 25^\circ\text{C}$ , per IEC61000-4-5 waveform.
3. Mounted with recommended minimum pad size, DC board FR-4



ON Semiconductor®

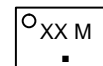
[www.onsemi.com](http://www.onsemi.com)



#### MARKING DIAGRAM



X2DFN2  
CASE 714AB



XX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

#### ORDERING INFORMATION

Device	Package	Shipping†
ESD7571N2T5G	X2DFN2 (Pb-Free)	8000 / Tape & Reel
SZESD7571N2T5G	X2DFN2 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

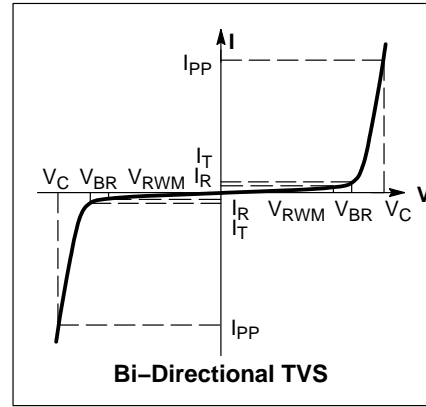
# ESD7571, SZESD7571

## ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current

\*See Application Note AND8308/D for detailed explanations of datasheet parameters.



## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Reverse Working Voltage	$V_{RWM}$				5.3	V
Breakdown Voltage	$V_{BR}$	$I_T = 1\text{ mA}$ (Note 4)	7.0			V
Reverse Leakage Current	$I_R$	$V_{RWM} = 5.3\text{ V}$		< 1	50	nA
Clamping Voltage	$V_C$	$I_{PP} = 1\text{ A}$ (Note 5)		13	15	V
Junction Capacitance	$C_J$	$V_R = 0\text{ V}, f = 1\text{ MHz}$ $V_R = 0\text{ V}, f = 1\text{ GHz}$		0.24 0.24	0.35 0.35	pF
Dynamic Resistance	$R_{DYN}$	TLP Pulse		0.8		$\Omega$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Breakdown voltage is tested from pin 1 to 2 and pin 2 to 1.
- Non-repetitive current pulse at  $25^\circ\text{C}$ , per IEC61000-4-5 waveform.

## TYPICAL CHARACTERISTICS

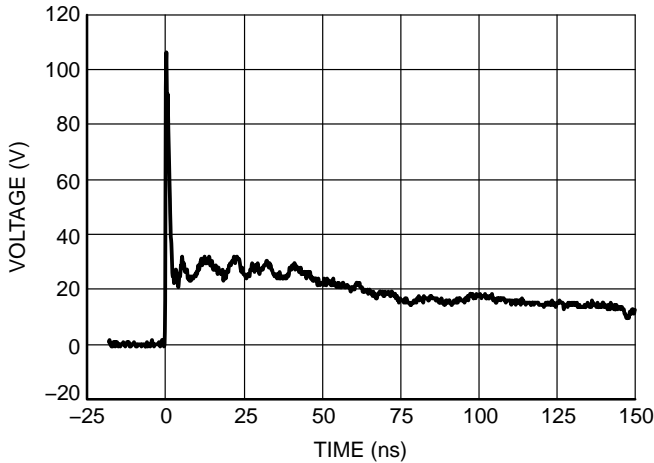


Figure 1. Typical IEC61000-4-2 + 8 kV Contact ESD Clamping Voltage

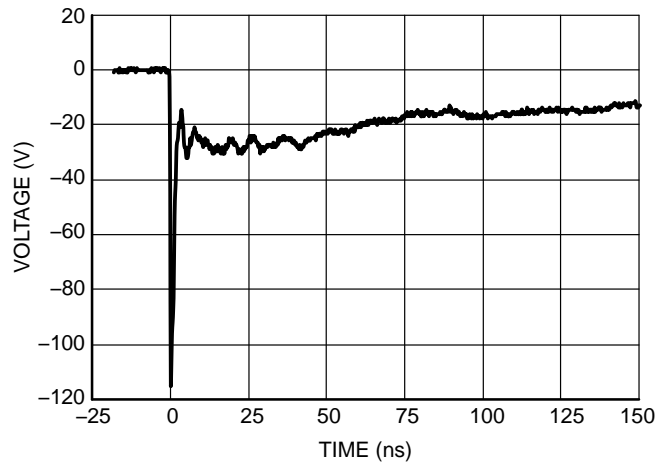


Figure 2. Typical IEC61000-4-2 - 8 kV Contact ESD Clamping Voltage

# ESD7571, SZESD7571

## IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8



Figure 3. IEC61000-4-2 Spec

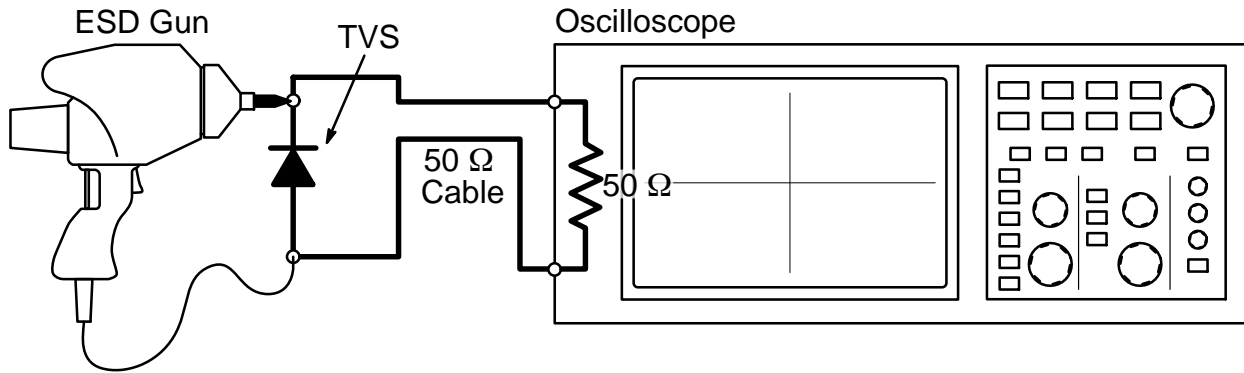


Figure 4. Diagram of ESD Clamping Voltage Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

### ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

# ESD7571, SZESD7571

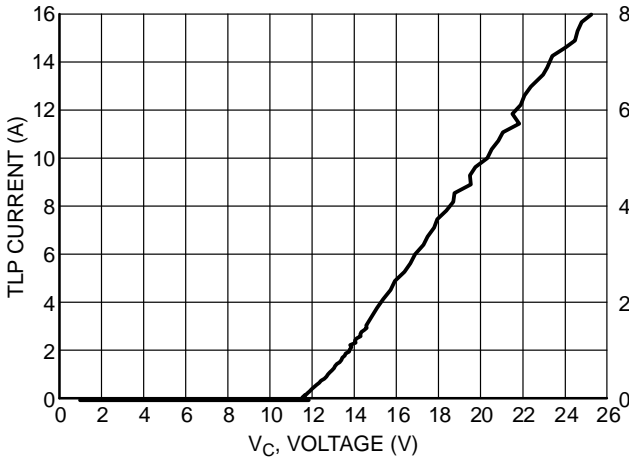


Figure 5. Typical Positive TLP IV Curve

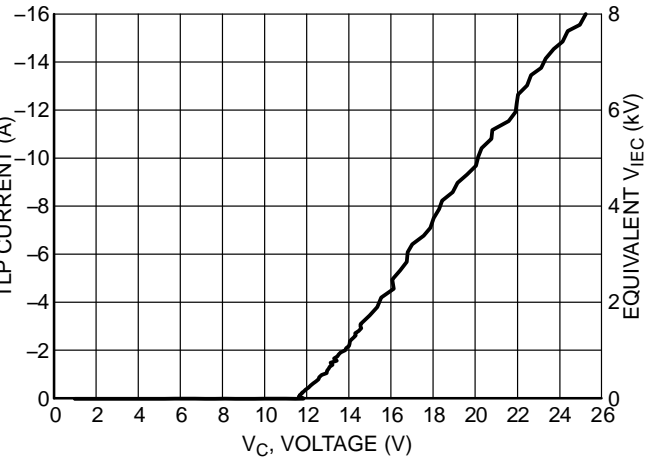


Figure 6. Typical Negative TLP IV Curve

NOTE: TLP parameter:  $Z_0 = 50 \Omega$ ,  $t_p = 100 \text{ ns}$ ,  $t_r = 300 \text{ ps}$ , averaging window:  $t_1 = 30 \text{ ns}$  to  $t_2 = 60 \text{ ns}$ .

## Transmission Line Pulse (TLP) Measurement

Transmission Line Pulse (TLP) provides current versus voltage (I-V) curves in which each data point is obtained from a 100 ns long rectangular pulse from a charged transmission line. A simplified schematic of a typical TLP system is shown in Figure 7. TLP I-V curves of ESD protection devices accurately demonstrate the product's ESD capability because the 10s of amps current levels and under 100 ns time scale match those of an ESD event. This is illustrated in Figure 8 where an 8 kV IEC 61000-4-2 current waveform is compared with TLP current pulses at 8 A and 16 A. A TLP I-V curve shows the voltage at which the device turns on as well as how well the device clamps voltage over a range of current levels.

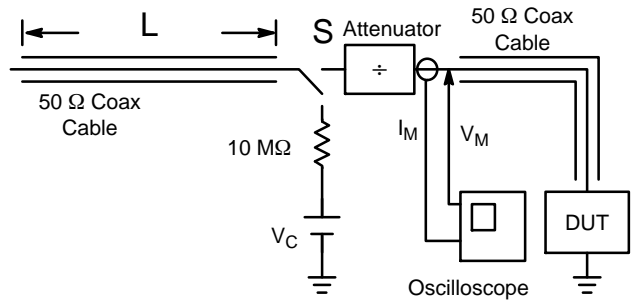


Figure 7. Simplified Schematic of a Typical TLP System

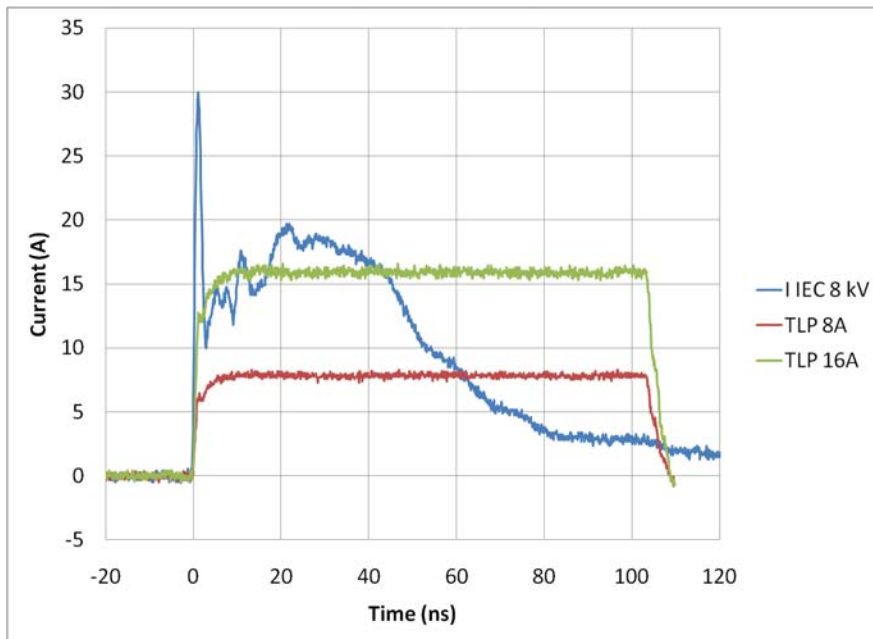


Figure 8. Comparison Between 8 kV IEC 61000-4-2 and 8 A and 16 A TLP Waveforms

# ESD7571, SZESD7571

## TYPICAL CHARACTERISTICS

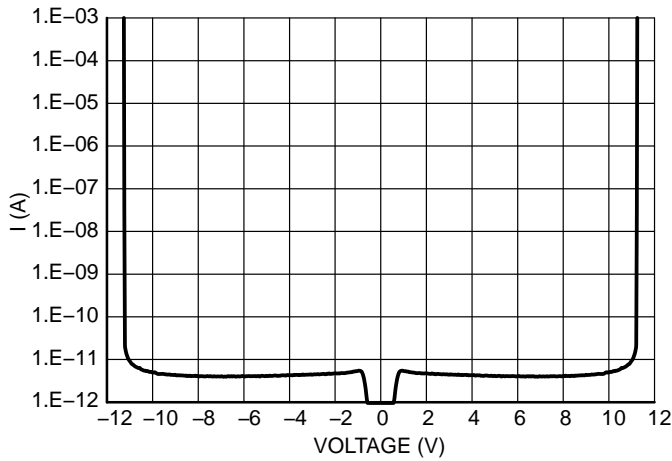


Figure 9. IV Characteristics

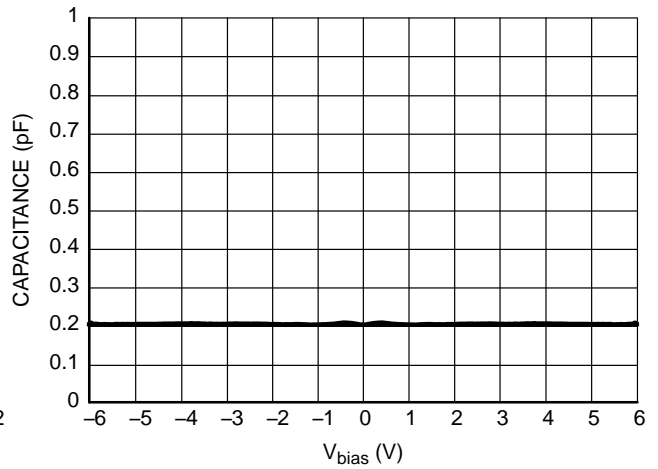


Figure 10. CV Characteristics

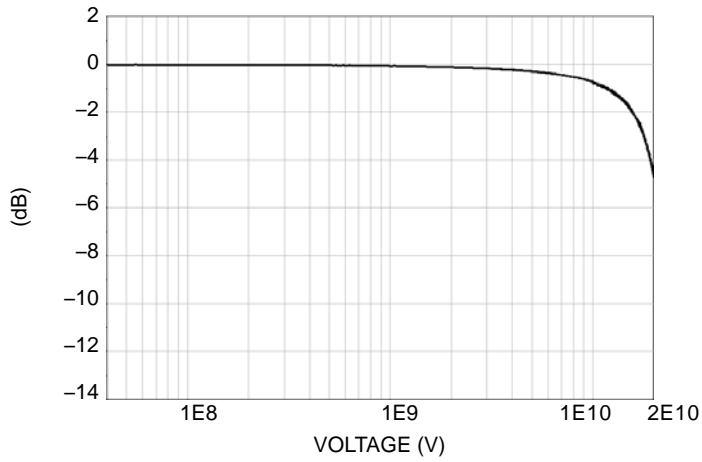


Figure 11. RF Insertion Loss

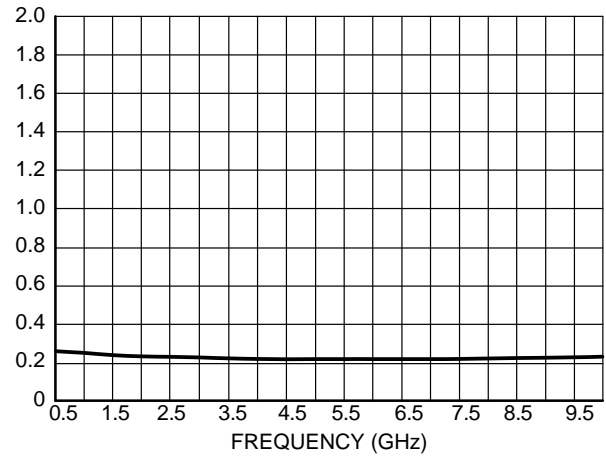
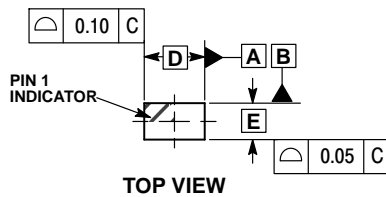


Figure 12. Capacitance over Frequency

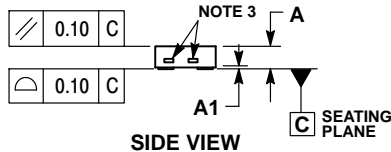
# ESD7571, SZESD7571

## PACKAGE DIMENSIONS

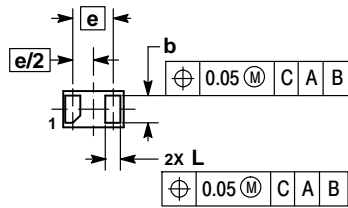
**X2DFN2 1.0x0.6, 0.65P**  
CASE 714AB  
ISSUE O



TOP VIEW



SIDE VIEW



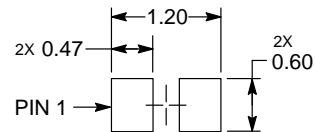
BOTTOM VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. EXPOSED COPPER ALLOWED AS SHOWN.

MILLIMETERS		
DIM	MIN	MAX
A	0.34	0.40
A1	---	0.05
b	0.45	0.55
D	1.00	BSC
E	0.60	BSC
e	0.65	BSC
L	0.20	0.30

### RECOMMENDED SOLDER FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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